

# Claims

- [c1] 1. A pixel structure, comprising:  
a scan line, disposed over a substrate;  
a redundant scan line, disposed over the scan line;  
a dielectric layer, disposed between the scan line and the redundant scan line, wherein at least three first contact holes are formed in the dielectric layer through which the scan line is electrically connected with the redundant scan line;  
a data line, disposed over the substrate;  
an active component, disposed adjacent to an intersection of the scan line and the data line; and  
a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line to write an image signal transmitted by the data line to the pixel electrode.
- [c2] 2. The pixel structure of claim 1, further comprising:  
a redundant data line, disposed under the data line, wherein the dielectric layer is disposed between the data line and the redundant data line, and the dielectric layer further has at least three second contact holes through which the data line is electrically connected with the re-

dundant data line.

- [c3] 3. The pixel structure of claim 1, further comprising:  
a redundant data line, disposed under the data line,  
wherein the dielectric layer is disposed between the data  
line and the redundant data line, and a third contact hole  
having a size in a range of about 20um to about a length  
of the data line is formed in the dielectric layer through  
which the data line is electrically connected with the re-  
dundant data line.
- [c4] 4. The pixel structure of claim 3, wherein the third con-  
tact hole comprises a rectangular hole, and a length of  
the rectangular hole is in a range of about 20um to  
about a length of the data line.
- [c5] 5. The pixel structure of claim 3, wherein the active  
component comprises a thin film transistor (TFT).
- [c6] 6. A pixel structure, comprising:  
a scan line, disposed over a substrate;  
a redundant scan line, disposed over the scan line;  
a dielectric layer, disposed between the scan line and the  
redundant scan line, wherein a first contact hole having a  
size in a range of about 20um to about a length of the  
scan line is formed in the dielectric layer through which  
the scan line is electrically connected with the redundant

scan line;  
a data line, disposed over the substrate;  
an active component, disposed adjacent to an intersection of the scan line and the data line; and  
a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line control to write an image signal transmitted by the data line to the pixel electrode.

[c7] 7. The pixel structure of claim 6, wherein the first contact hole comprises a rectangular hole having a length in a range of about 20um to about a length of the scan line.

[c8] 8. The pixel structure of claim 6, further comprising:  
a redundant data line, disposed under the data line,  
wherein the dielectric layer is disposed between the data line and the redundant data line, and at least three second contact holes are formed in the dielectric layer through which the data line is electrically connected with the redundant data line.

[c9] 9. The pixel structure of claim 6, further comprising:  
a redundant data line, disposed under the data line,  
wherein the dielectric layer is disposed between the data line and the redundant data line between, and a third contact hole having a size in a range of about 20um to

about a length of the data line through which the dielectric layer the data line is electrically connected with the redundant data line.

[c10] 10. The pixel structure of claim 9, wherein the third contact hole comprises a rectangular hole having a length in a range of about 20um to about a length of the data line.

[c11] 11. The pixel structure of claim 6, wherein the active component comprises a thin film transistor (TFT).

[c12] 12. A pixel structure, comprising:  
a scan line, disposed over a substrate;  
a data line, disposed over the substrate;  
a redundant data line, disposed under the data line;  
a dielectric layer, disposed between the data line and the redundant data line, wherein at least three first contact holes are formed in the dielectric layer through which the data line is electrically connected with the redundant data line;  
an active component, disposed adjacent to an intersection of the scan line and the data line; and  
a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line to write an image signal transmitted by the data line to the pixel electrode.

- [c13] 13. The pixel structure of claim 12, wherein the active component comprises a thin film transistor (TFT).
- [c14] 14. A pixel structure, comprising:  
a scan line, disposed over a substrate;  
a data line, disposed over the substrate;  
a redundant data line, disposed under the data line;  
a dielectric layer, disposed between the data line and the redundant data line, wherein a first contact hole having a size in a range of about 20um to about a length of the data line is formed in the dielectric layer through which the data line is electrically connected with the redundant data line;  
an active component, disposed adjacent to an intersection of the scan line and the data line; and  
a pixel electrode, electrically connected to the active component, wherein the active component is controlled by the scan line control to write an image signal transmitted by the data line to the pixel electrode.
- [c15] 15. The pixel structure of claim 14, wherein the first contact hole comprises a rectangular hole having a length in a range of about 20um to about a length of the data line.
- [c16] 16. The pixel structure of claim 14, wherein the active component comprises a thin film transistor (TFT).

